

Product data sheet

## 1. General description

Hyperfast power diode in a SOD113A (2-lead TO-220-F) plastic package.

## 2. Features and benefits

- Fast switching
- Isolated plastic package
- Low leakage current
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses in associated MOSFET or IGBT

## 3. Applications

- Active PFC in air conditioner
- High frequency switched-mode power supplies
- Continuous Current Mode (CCM) Power Factor Correction (PFC)

## 4. Quick reference data

Table 1. Quie	ck reference data							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V <sub>RRM</sub>	repetitive peak reverse voltage			-	-	600	V	
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5; T <sub>h</sub> ≤ 61 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3		-	-	10	A	
Static characte	eristics				·	·		
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>		-	1.3	2	V	
Dynamic chara	Dynamic characteristics							
t <sub>rr</sub>	reverse recovery time	$I_F$ = 1 A; $V_R$ = 30 V; $dI_F/dt$ = 200 A/µs; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>		-	12	18	ns	





# 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode	mb	К — А
2	А	anode		001aaa020
mb	n.c.	mounting base; isolated	TO-220F (SOD113A)	

# 6. Ordering information

Table 3. Ordering in	formation					
Type number	Package					
	Name	Description	Version			
BYC10X-600P	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220F "full pack"	SOD113A			

## 7. Marking

Table 4.     Marking codes	
Type number	Marking code
BYC10X-600P	BYC10X-600P

# 8. Limiting values

## Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V <sub>RRM</sub>	repetitive peak reverse voltage			-	600	V
V <sub>RWM</sub>	crest working reverse voltage			-	600	V
V <sub>R</sub>	reverse voltage	DC		-	600	V
I <sub>F(AV)</sub>	average forward current	δ = 0.5; T <sub>h</sub> ≤ 61 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3		-	10	A
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5; $t_p$ = 25 µs; $T_h$ $\leq$ 61 °C; square-wave pulse		-	20	A
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Symbol	Parameter	Conditions	Min	Max	Unit
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	150	A
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	165	A
T <sub>stg</sub>	storage temperature		-65	175	°C
Tj	junction temperature		-	175	°C

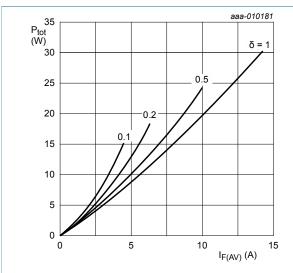
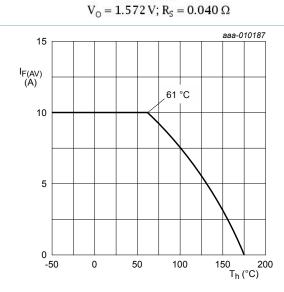
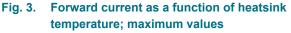


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$ 





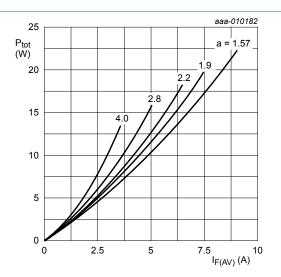
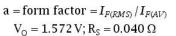


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values



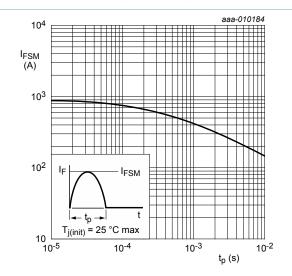


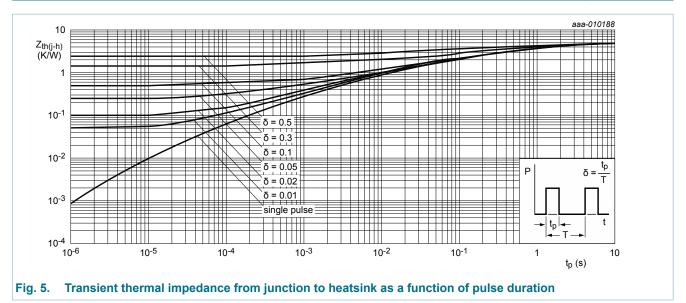
Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

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## 9. Thermal characteristics

Table 6. T	hermal characteristics		 			
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-h)</sub>	thermal resistance from junction to heatsink	with heatsink compound; Fig. 5	-	-	4.8	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	-	55	-	K/W



## **10. Isolation characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>isol(RMS)</sub>	RMS isolation voltage	50 Hz $\leq$ f $\leq$ 60 Hz; RH $\leq$ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C <sub>isol</sub>	isolation capacitance	f = 1 MHz; from cathode to external heatsink	-	10	-	pF

## **11. Characteristics**

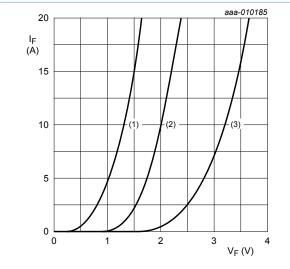
Table 8. C	haracteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static characteristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	-	2.5	3.2	V
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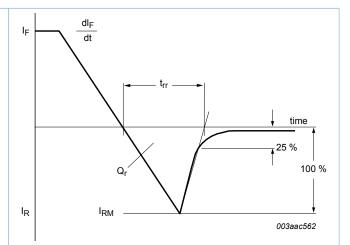
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>	-	1.3	2	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C	-	-	10	μA
		V <sub>R</sub> = 600 V; T <sub>j</sub> = 150 °C	-	-	0.8	mA
Dynamic cl	haracteristics	· · ·	I			
Q <sub>r</sub> recovered	recovered charge	I <sub>F</sub> = 10 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/ μs; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	26	-	nC
		I <sub>F</sub> = 10 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/ μs; T <sub>j</sub> = 125 °C; <u>Fig. 7</u>	-	83	-	nC
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	12	18	ns
		$I_F$ = 10 A; V <sub>R</sub> = 400 V; dI <sub>F</sub> /dt = 500 A/ µs; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	19	-	ns
		I <sub>F</sub> = 10 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/ μs; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	26	-	ns
		I <sub>F</sub> = 10 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/ μs; T <sub>j</sub> = 125 °C; <u>Fig. 7</u>	-	34	-	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F$ = 10 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/ µs; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	2	-	A
		I <sub>F</sub> = 10 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/ μs; T <sub>j</sub> = 125 °C; <u>Fig. 7</u>	-	4.8	-	A



# Fig. 6. Forward current as a function of forward voltage

(1) T<sub>j</sub> = 150 °C; typical values;
(2) T<sub>j</sub> = 150 °C; maximum values;
(3) T<sub>j</sub> = 25 °C; maximum values;
V<sub>O</sub> = 1.572 V; R<sub>S</sub> = 0.040 Ω

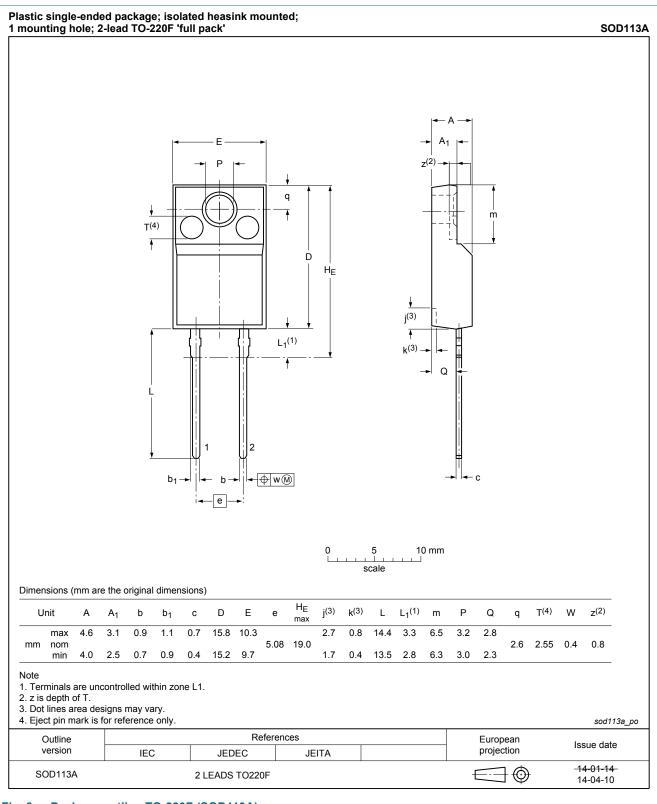






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## 12. Package outline



### Fig. 8. Package outline TO-220F (SOD113A)

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